

TECHNICAL DATA DATA SHEET 5034, REV. A

LOW RDS HERMETIC POWER MOSFET - N-CHANNEL

FEATURES:

- 100 Volt, 0.013 Ohm, 90A MOSFET
- Isolated Hermetic Metal Package
- Ultra Low R_{DS (on)}

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_{\rm C}$ = 25°C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
ON-STATE DRAIN CURRENT	I _{D25}	-	-	55*	Amps
PULSED DRAIN CURRENT	I _{DM}	-	-	240	Amps
OPERATING AND STORAGE TEMPERATURE	T_J/T_{STG}	-55	-	+150	°C
TOTAL DEVICE DISSIPATION	P_{D}	-	-	210	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{\theta JC}$	-	-	0.6	°C/W

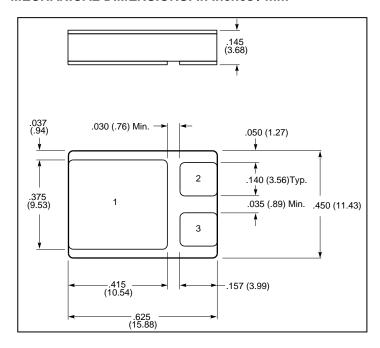
Note: * current limited by package; die rating is 90A

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV _{DSS}	100	-	-	Volts
$V_{GS} = 0V, I_D = 250\mu A$					
STATIC DRAIN TO SOURCE ON STATE RESISTANCE	R _{DS(ON)}				Ω
$V_{GS} = 10V, I_{D} = 30A$		-	0.013	0.015	
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	2	-	4	Volts
FORWARD TRANSCONDUCTANCE	g_{fs}	25	-	-	S(1/Ω)
$V_{DS} = 15V, I_{D} = 30A$					
ZERO GATE VOLTAGE DRAIN CURRENT					
$V_{DS} = 0.8 \text{ x Max. rating}, V_{GS} = 0V, T_{J} = 25^{\circ}C$	I_{DSS}	-	-	1	μΑ
$T_{J} = 125^{\circ}C$				50	
GATE TO SOURCE LEAKAGE FORWARD V _{GS} = 20V	I_{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20V$				-100	
TURN ON DELAY TIME $V_{DD} = 50V$	$t_{d(ON)}$	-	20	-	
RISE TIME $I_D = 55A$	t _r		110		nsec
TURN OFF DELAY TIME V _{GS} =10V			0.5		
	t _{d(OFF)}		65		
FALL TIME $R_G = 2.5\Omega$	t _f		100		
DIODE FORWARD VOLTAGE $I_F = 30A, V_{GS} = 0V$	V_{SD}	-	1.0	1.2	Volts
Pulse test, $t \le 300 \mu s$, duty cycle $d \le 2 \%$					
REVERSE RECOVERY TIME $T_J = 25$ °C,					
$I_F=30A, V_R=100V$	t _{rr}	-	70	140	nsec
di/dt = 100A/μsec					
INPUT CAPACITANCE $V_{GS} = 0 V$,	C_{iss}	-	8700	-	
OUTPUT CAPACITANCE $V_{DS} = 25 \text{ V},$	C_{oss}		740		рF
REVERSE TRANSFER CAPACITANCE f = 1.0MHz	C_{rss}		450		

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MECHANICAL DIMENSIONS: in Inches / mm



SMD-1

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
N CHANNEL MOSFET IN A LCC-3P PACKAGE	DRAIN	SOURCE	GATE

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